

IN THE CLAIMS

Per the revised amendment practice, a complete listing of all claims in the application follows.

Claims 1-44 (Canceled).

45. (Currently amended) A method of providing a material in a site between metal features on a wafer, comprising:

performing a deposition of said material over said wafer in said site, wherein said deposition occurs at a greater rate within said site than above said features; and etching said material in the same general site used to perform said deposition, wherein said step of etching further comprises etching generally simultaneously with performing said deposition.

46. (Currently amended) The method in claim 45 A method of providing a material in a site between metal features on a wafer, comprising:

performing a deposition of said material in said site, wherein said step of performing a deposition further comprises depositing a polymer on said wafer; and etching said material in the same general site used to perform said deposition, wherein said step of etching further comprises etching generally simultaneously with performing said deposition.

47. (New) The method in claim 45, wherein said deposition occurs above said features.

48. (New) A method of providing a material in a site between metal features on a wafer, comprising:

performing a deposition of said material in said site; and plasma etching said material in the same general site used to perform said deposition, wherein said etching further comprises etching generally simultaneously with performing said deposition.

49. (New) The method in claim 48, wherein said step of performing a deposition comprises performing a plasma deposition.